

EXACT Interconnect Parasitic Characterization



EXACT™ Interconnect Parasitic Characterization delivers the most accurate interconnect models for nanometer semiconductor processes and generates layout parameter extraction (LPE) rule files for leading full chip extraction tools. EXACT's powerful 3D field solvers support xCalibre™, Calibre xRC™, Diva™, Assura RCX™, and Dracula™ LPE.

- Powerful 3D solver supports non-planar semiconductor profiles for accurately modeling irregular etch profiles, dual damascene, and low-K dielectrics
- 3D field solver calculates interconnect capacitance models to deliver highest accuracy LPE rule files without compromising extraction performance
- Intuitive and user-friendly graphical interface for process layer description and test structure definition for beginner and experienced process technology developers
- Standard mode of operation handles most conventional processes whereas advanced mode can be used for more complex and non-planar process definition
- Integrated scripting language provides custom LPE rule files for other extraction tools
- Powerful statistical analysis module option available to calculate variations of capacitance using known process margins to account for interconnect process variations

Ease of Use and Adoption

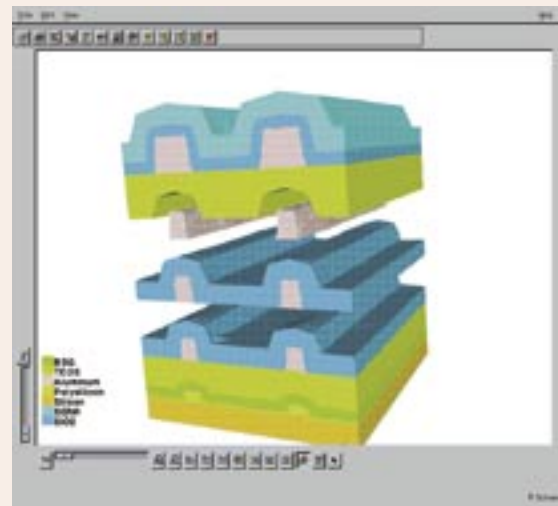
- Easy to use, menu-driven graphical interface for process layer definition and conversion of legacy Raphael™ files
- Easy LPE rule generation with LISA™ scripting language
- Menu-driven parameterized layout generator for test structure and pattern generation
- Flexible architecture for fitting raw parasitic data into a wide range of custom equations for xCalibre™, Calibre xRCT™, and Assura-RCX™/Diva™/Dracula™ LPE

Productivity and Versatility

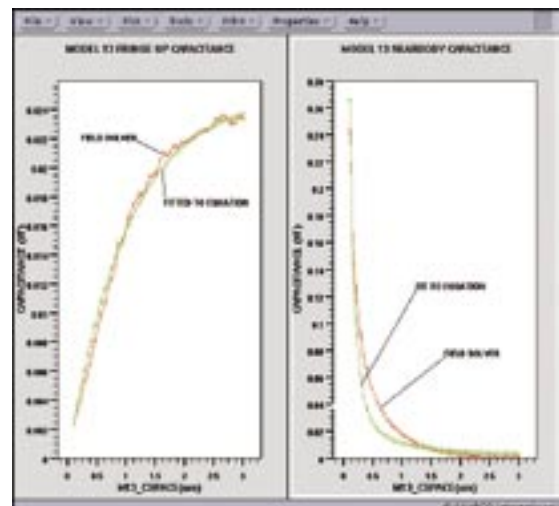
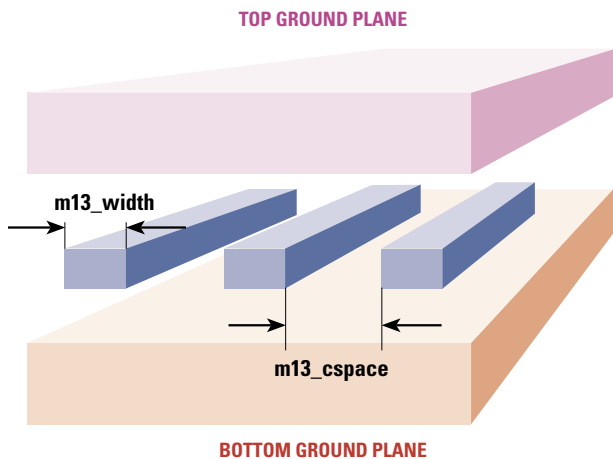
- Batch mode operation allows pipeline submitting of overnight runs
- Advanced mode operation is designed to allow experienced users to have more control over the field solver to address more complex process topology
- Inclusion of process variables in experiments to perform statistical analysis on interconnect capacitance variations
- Easy to understand extracted capacitance tables that facilitate the analysis of effects on interconnect due to various process change or experiment
- Automatic deck generation and submission to 3D field solver



Front-end to EXACT.



Multilevel metal process with conformally deposited, non-planar multiple dielectrics.



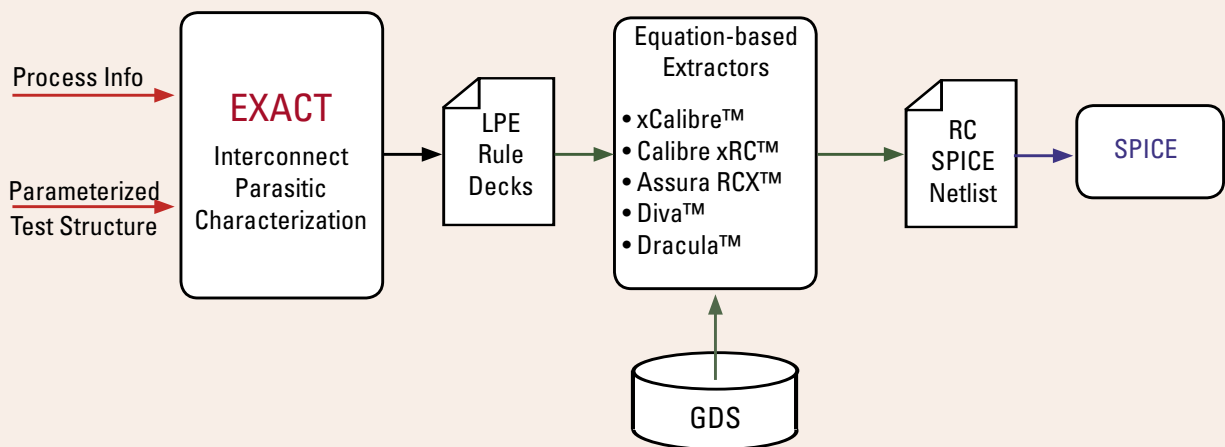
Field solver results and fitted equation for the structure on the left.

**Advanced Semiconductor
Process Support**

Interconnect parasitic capacitance modeling support for

- Planar and non-planar dielectrics
- Low-K dielectric and copper damascene process
- Conformal dielectrics deposition
- Sub-wavelength lithographic effects due to optical proximity correction (OPC)
- Process variations impact on interconnect capacitance
- Statistical analysis and worst-case parasitic analysis by applying known process margins to extracted data
- Powerful 3D solver supports non-planar semiconductor profiles for accurately modeling irregular etch profiles, dual damascene, and low-K dielectrics
- 3D field solver calibrates interconnect capacitance models to deliver highest accuracy LPE rule files without compromising extraction performance
- Built-in Optimizer enables improved fitting and process optimization

EXACT takes process information and produces LPE rule decks.



```

CAPACITANCE INTERDIGIT FRINGE metal2
{
    PARAMETER C
    MAX_DISTANCE = 5
    MAX_WIDTH = 3
    C = 0.0
    IF (distance() > 0.1) {
        C = 0.0101*(1.0 - exp(-1.45*(distance()+0.015)))*length()
    }
    IF (distance() <= 0.1) {
        C = 0.010442* length()
    }
}

CAPACITANCE NEARBODY poly1
{
    PARAMETER C
    MAX_WIDTH = 3
    MAX_DISTANCE = 3
    C = 0.010742*length()*pow(1.0, 0.516148)*1.0*(exp((-distance()+1.40124)-0.64943)
    + (0.0077904/pow(distance(), 1.3288)))
}
    
```

Mentor Graphics xCalibre™/Calibre xRC™ rule file generated by EXACT.

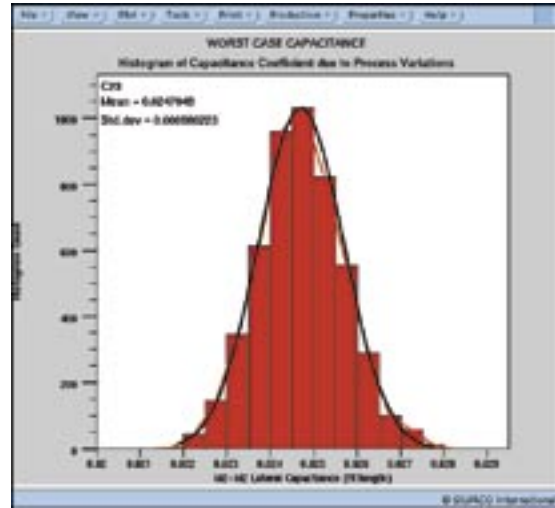
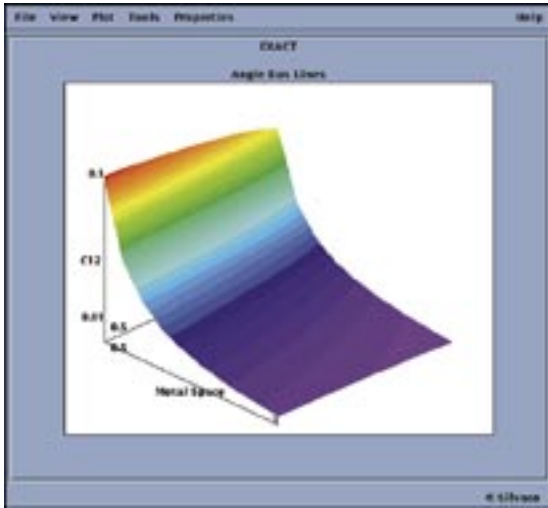
```

„Give rule file for same layer nearby capacitance
„Use Onetarray like structure

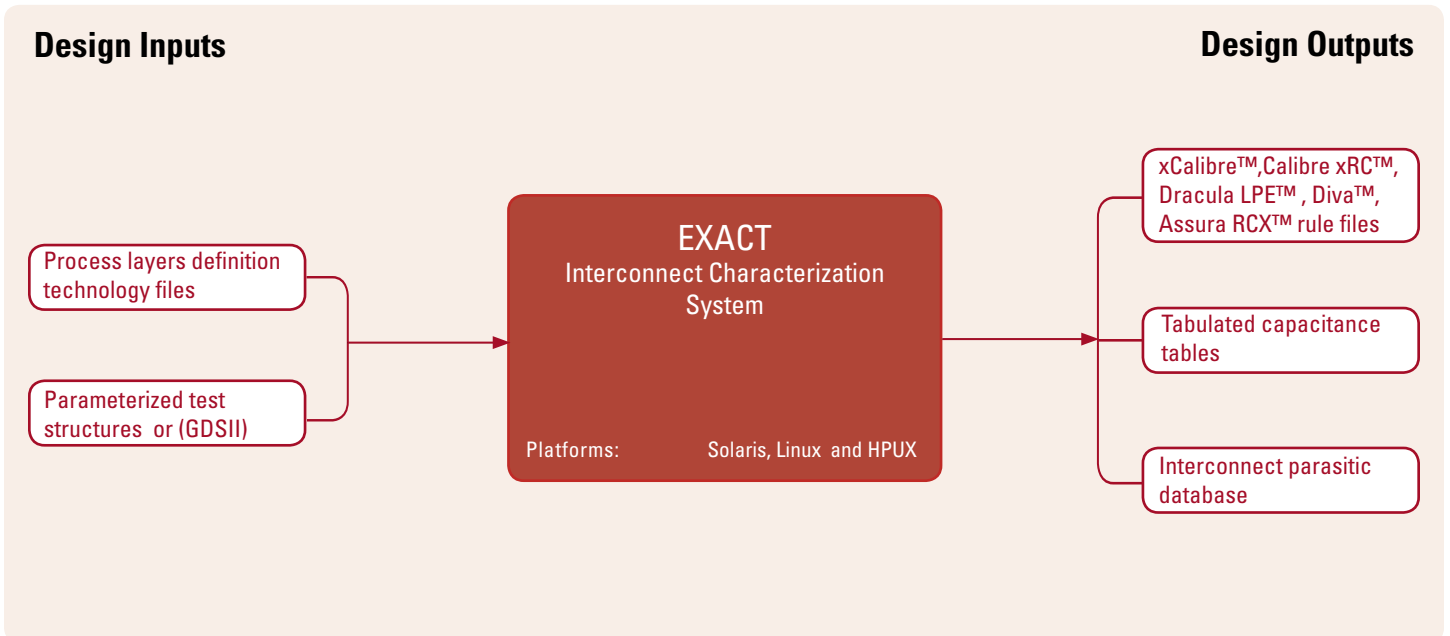
metal2_metal2_fcap=0.010742*length()
metal2
calculate(1+((0.010742)/(pow((1+0.121027)*1.30164))))
PG M1layer_metal2
sep = 1.358
opposite
shielded
diffrec

metal2_metal2_fcap=0.010742*length()
metal2
calculate(1+((0.010742)/(pow((1+0.121027)*1.30164))))
PG M1layer_metal2
sep = 1.358
opposite
shielded
diffrec
    
```

Cadence Diva™ rule file generated by EXACT.



Variation of capacitance coefficient with process variables can be seen graphically (left) or analyzed statistically (right). The histogram shows the expected distribution in lateral capacitance with known margin on metal geometry.



© 2003 Silvaco International. All rights reserved. Silvaco, Silvaco logo, EXACT and LISA are trademarks of Silvaco International. All others are properties of their respective holders. Rev. 072203_12

SILVACO

USA Headquarters:

Silvaco International
 4701 Patrick Henry Drive, Bldg. 2
 Santa Clara, CA 95054 USA
 Phone: 408-567-1000

Fax: 408-496-6080
 sales@silvaco.com
 www.silvaco.com

Worldwide:

Japan: jpsales@silvaco.com
 Korea: krsales@silvaco.com
 Taiwan: twsales@silvaco.com
 Singapore: sgsales@silvaco.com
 UK: uksales@silvaco.com
 France: frsales@silvaco.com
 Germany: desales@silvaco.com